

Feature

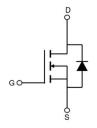
• 100V,60A

$$\begin{split} &R_{\text{DS (ON)}} < 9.5 \text{m}\,\Omega\,\text{@V}_{\text{GS}} = 10 \text{V} \quad \text{(TYP:7.5m}\,\Omega\,\text{)} \\ &R_{\text{DS (ON)}} < 13 \text{m}\,\Omega\,\text{@V}_{\text{GS}} = 4.5 \text{V} \quad \text{(TYP:10.5m}\,\Omega\,\text{)} \end{split}$$

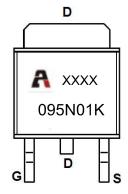
- Split Gate Trench Technology
- Lead free product is acquired
- Excellent R DS (ON) and Low Gate Charge

Application

- PWM applications
- Load Switch
- Power management



Schematic Diagram



Marking and pin assignment

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
G095N01K	APG095N01K	TO-252	13 inch	-	2500

ABSOLUTE MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _G s	±20	V
Continuous Drain Current (T _a =25℃)	ΙD	60	A A A
Continuous Drain Current (T _a =100℃)	I _D	38	
Pulsed Drain Currenr (1)	І _{DМ}	240	
Singel Pulsed Avalanche Energy (2)	Eas	90	mJ
Power Dissipation	PD	63	W
Thermal Resistance from Junction to Case	Rejc	2.0	°C/W
Junction Temperature	TJ	150	$^{\circ}$
Storage Temperature	T _{STG}	-55~ +150	$^{\circ}$



MOSFET ELECTRICAL CHARACTERISTICS(T_a=25℃ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	100	_	-	V
Zero gate voltage drain current	IDSS	V _{DS} =80V, V _{GS} = 0V	-	-	1	μA
Gate-body leakage current	I _{GSS}	V_{GS} = ± 20 V, V_{DS} = 0V	-	-	±100	nA
Gate threshold voltage(3)	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.2	2.0	2.5	V
Drain-source on-resistance ⁽³⁾	D	V _{GS} =10V, I _D =20A		7.5	9.5	0
Drain-source on-resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =10A	-	10.5	13	mΩ
Forward Threshold Voltage	g fs	V _{DS} =5V, I _D =20A	-	13.5	-	S
Gate Resistance	Rg	$V_{DS} = V_{GS} = 0V$, f = 1MHz	-	1.94	-	Ω
Dynamic characteristics						
Input Capacitance	Ciss		-	2122	-	pF
Output Capacitance	Coss	V _{DS} =50V, V _{GS} =0V, f =1MHz	-	618	-	
Reverse Transfer Capacitance	C _{rss}	-	-	25	-	
Switching characteristics						
Turn-on delay time	t _{d(on)}		-	17	-	ns
Turn-on rise time	tr	V _{DD} =50V, I _D =20A,	-	4	-	
Turn-off delay time	t _{d(off)}	V_{GS} =10V, R_{G} =3 Ω	-	32	-	
Turn-off fall time	t _f		-	8	-	
Total Gate Charge	Qg	\/D0_50\/ ID_00A	-	41.8	-	
Gate-Source Charge		VDS=50V, ID=20A, VGS=10V	-	9	-	nC
Gate-Drain Charge	Qgd	- VGS-10V	-	10	-	
Reverse Recovery Chrage	Qrr	I _F =20A,di/dt=100A/us		71.5		nC
Reverse Recovery Time Trr		I _F =20A,di/dt=100A/us		50.5		ns
Source-Drain Diode characteristics	·	•	·	•		
Diode Forward voltage ⁽³⁾	V _{DS}	V _{GS} =0V, I _S =20A	-	-	1.2	V
Diode Forward current ⁽⁴⁾	orward current ⁽⁴⁾ Is		-	-	60	Α

Notes:

- 1. Repetitive Rating: pulse width limited by maximum junction temperature
- 2. EAS Condition:TJ=25°C,VDD=50V,RG=25 Ω ,L=0.5mH
- 3. Pulse Test: pulse width≤300µs, duty cycle≤2%
- 4. Surface Mounted on FR4 Board,t≤10 sec



Typical Performance Characteristics

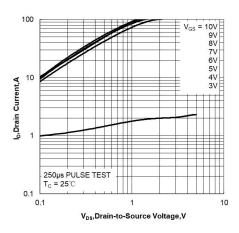


Figure 1. Output Characteristics

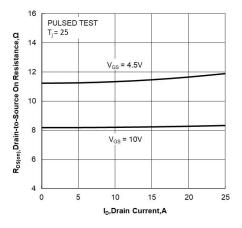


Figure 3. Drain-to-Source On Resistance vs Drain Current

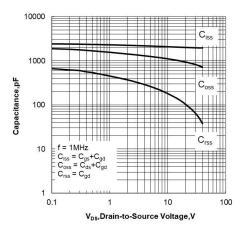


Figure 5. Capacitance Characteristics

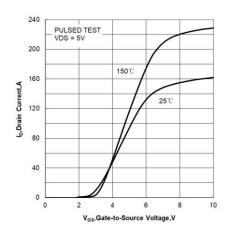


Figure 2. Transfer Characteristics

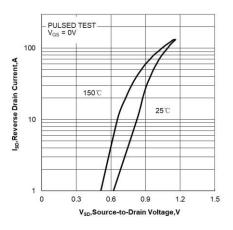


Figure 4. Body Diode Forward Voltage vs Source Current and Temperature

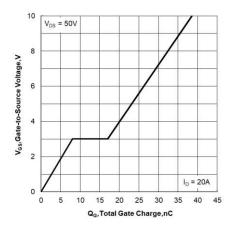


Figure 6. Gate Charge Characteristics



DATA SHEET

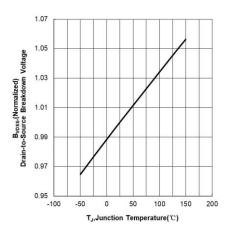


Figure 7. Normalized Breakdown Voltage vs Junction Temperature

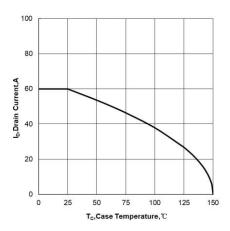


Figure 9. Maximum Continuous Drain Current vs Case Temperature

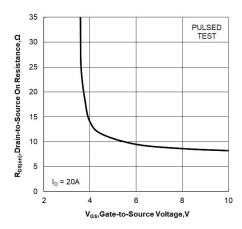


Figure 11. Drain-to-Source On Resistance vs Gate

Voltage and Drain Current

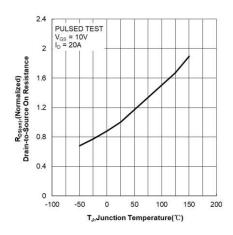


Figure 8. Normalized On Resistance vs

Junction Temperature

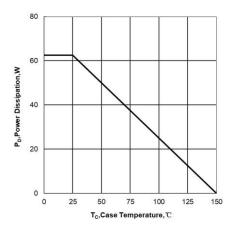


Figure 10. Maximum Power Dissipation vs Case Temperature

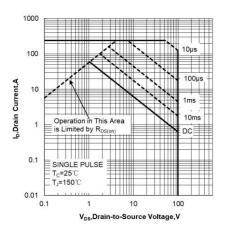


Figure 12. Maximum Safe Operating Area



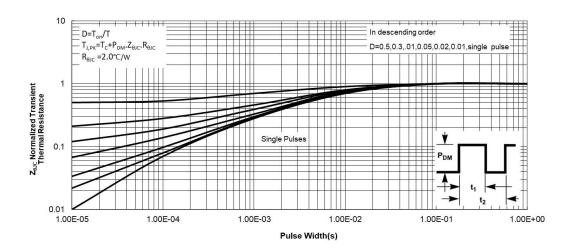
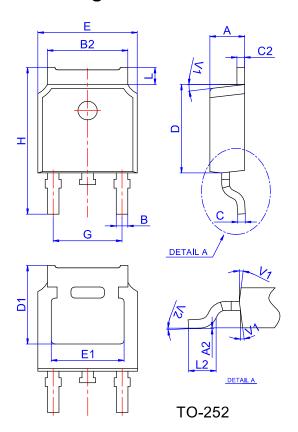


Figure 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

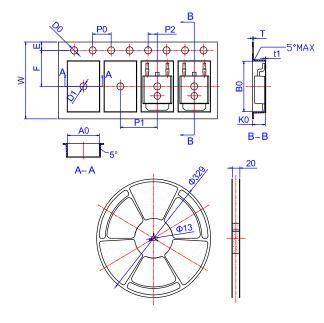


TO-252 Package Information



	Dimensions							
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Ref.		Millimete	rs	Inches				
	Min.	Тур.	Max.	Min.	Тур.	Max.		
Α	2.10		2.50	0.083		0.098		
A2	0		0.10	0		0.004		
В	0.66		0.86	0.026		0.034		
B2	5.18		5.48	0.202		0.216		
С	0.40		0.60	0.016		0.024		
C2	0.44		0.58	0.017		0.023		
D	5.90		6.30	0.232		0.248		
D1		5.30REF		0.209REF				
E	6.40		6.80	0.252		0.268		
E1	4.63			0.182				
G	4.47		4.67	0.176		0.184		
Н	9.50		10.70	0.374		0.421		
L	1.09		1.21	0.043		0.048		
L2	1.35		1.65	0.053		0.065		
V1		7°			7°			
V2	0°		6°	0°		6°		

Reel Spectification-TO-252



	Dimensions							
Ref.	Millimeters			Inches				
	Min.	Тур.	Max.	Min.	Тур.	Max.		
W	15.90	16.00	16.10	0.626	0.630	0.634		
E	1.65	1.75	1.85	0.065	0.069	0.073		
F	7.40	7.50	7.60	0.291	0.295	0.299		
D0	1.40	1.50	1.60	0.055	0.059	0.063		
D1	1.40	1.50	1.60	0.055	0.059	0.063		
P0	3.90	4.00	4.10	0.154	0.157	0.161		
P1	7.90	8.00	8.10	0.311	0.315	0.319		
P2	1.90	2.00	2.10	0.075	0.079	0.083		
A0	6.85	6.90	7.00	0.270	0.271	0.276		
В0	10.45	10.50	10.60	0.411	0.413	0.417		
K0	2.68	2.78	2.88	0.105	0.109	0.113		
Т	0.24		0.27	0.009		0.011		
t1	0.10			0.004				
10P0	39.80	40.00	40.20	1.567	1.575	1.583		